

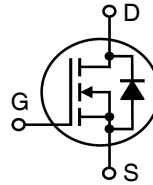
X2-Class HiperFET™ Power MOSFET

IXFP18N65X2M

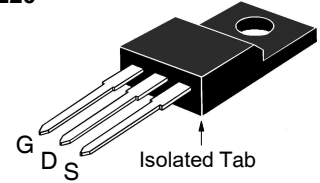
$$\begin{aligned} V_{DSS} &= 650V \\ I_{D25} &= 18A \\ R_{DS(on)} &\leq 200m\Omega \end{aligned}$$

(Electrically Isolated Tab)

N-Channel Enhancement Mode



OVERMOLDED
TO-220



G = Gate
S = Source
D = Drain

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	650	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	650	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$, Limited by T_{JM}	18	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	22	A
I_A	$T_C = 25^\circ\text{C}$	4	A
E_{AS}	$T_C = 25^\circ\text{C}$	300	mJ
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	50	V/ns
P_D	$T_C = 25^\circ\text{C}$	36	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ\text{C}$
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, 1 Minute	2500	V~
M_d	Mounting Torque	1.13 / 10	Nm/lb.in
Weight		2.5	g

Features

- International Standard Package
- Plastic Overmolded Tab
- High Voltage Package
- Low $R_{DS(ON)}$ and Q_G
- Avalanche Rated
- 2500V~ Electrical Isolation
- Low Package Inductance

Advantages

- High Power Density
- Easy to Mount
- Space Savings

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- PFC Circuits
- AC and DC Motor Drives
- Robotics and Servo Controls

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = 250\mu A$	650		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 1.5mA$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			25 μA 1.5 mA
$R_{DS(on)}$	$V_{GS} = 10V$, $I_D = 9A$, Note 1		164	200 m Ω

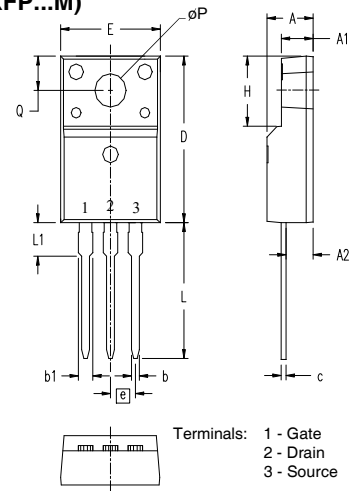
Symbol	Test Conditions ($T_J = 25^{\circ}\text{C}$, Unless Otherwise Specified)	Characteristic Values			
		Min.	Typ.	Max	
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 9\text{A}$, Note 1	8	13	S	
R_{Gi}	Gate Input Resistance		3.5	Ω	
C_{iss} C_{oss} C_{rss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		1520	pF	
			1100	pF	
			1.8	pF	
Effective Output Capacitance					
$C_{o(er)}$ $C_{o(tr)}$	Energy related Time related	$V_{GS} = 0\text{V}$ $V_{DS} = 0.8 \cdot V_{DSS}$	72 250	pF pF	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 9\text{A}$ $R_G = 10\Omega$ (External)		20 30 50 26	ns ns ns ns	
$Q_{g(on)}$ Q_{gs} Q_{gd}		$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 9\text{A}$		29 9 11	nC nC nC
R_{thJC} R_{thCS}				0.50	3.5 $^{\circ}\text{C/W}$ $^{\circ}\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max
I_S	$V_{GS} = 0\text{V}$			18 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			72 A
V_{SD}	$I_F = I_S$, $V_{GS} = 0\text{V}$, Note 1			1.4 V
t_{rr}	$I_F = 9\text{A}$, $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$		135	ns
Q_{RM}			840	nC
I_{RM}			12.5	A

Note 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

OVERMOLDED TO-220 (IXFP...M)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.177	.193	4.50	4.90
A1	.092	.108	2.34	2.74
A2	.101	.117	2.56	2.96
b	.028	.035	0.70	0.90
b1	.050	.058	1.27	1.47
c	.018	.024	0.45	0.60
D	.617	.633	15.67	16.07
E	.392	.408	9.96	10.36
e	.100 BSC		2.54 BSC	
H	.255	.271	6.48	6.88
L	.499	.523	12.68	13.28
L1	.119	.135	3.03	3.43
ØP	.121	.129	3.08	3.28
Q	.126	.134	3.20	3.40

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065B1	6,683,344	6,727,585	7,005,734B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123B1	6,534,343	6,710,405B2	6,759,692	7,063,975B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728B1	6,583,505	6,710,463	6,771,478B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

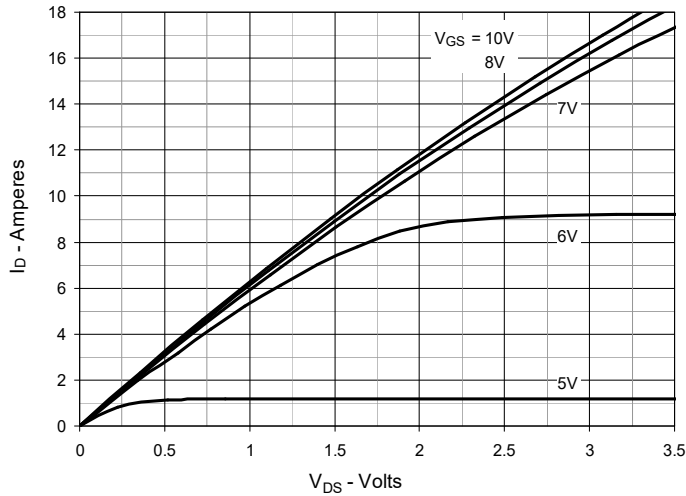


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

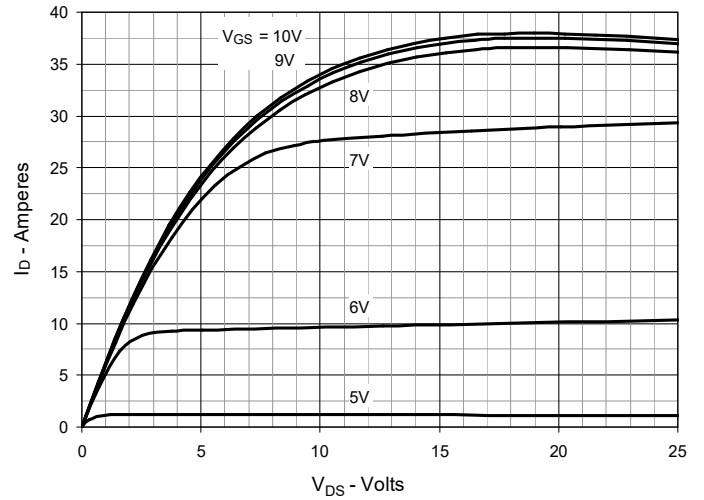


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

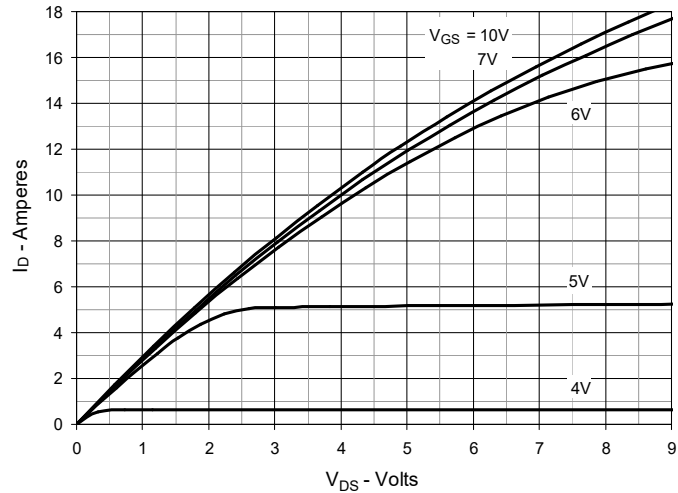


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 9\text{A}$ Value vs. Junction Temperature

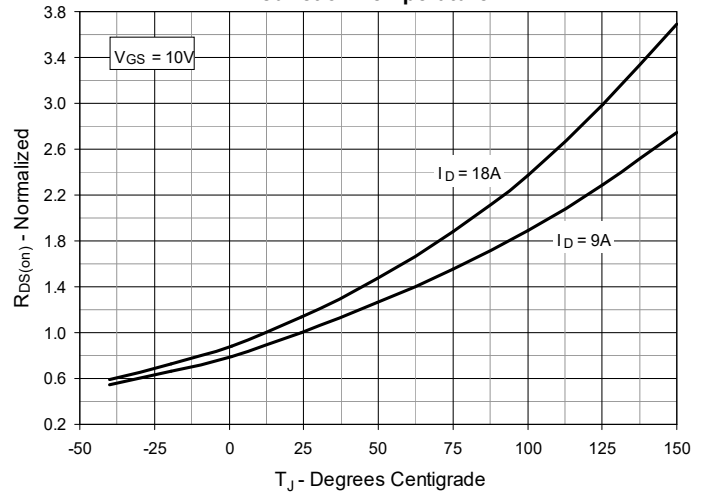


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 9\text{A}$ Value vs. Drain Current

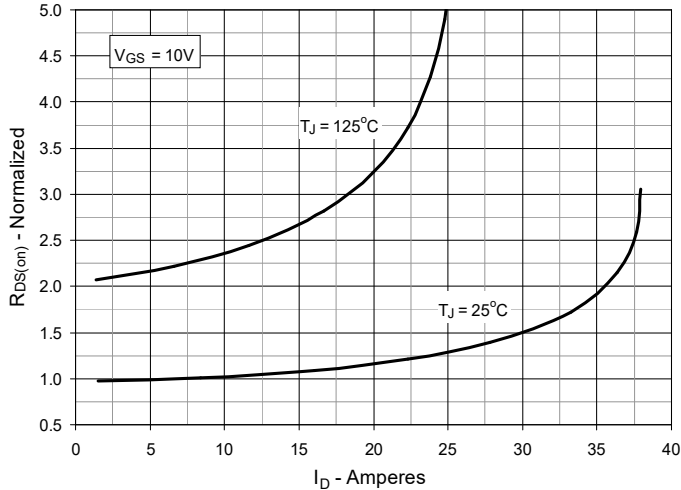


Fig. 6. Normalized Breakdown & Threshold Voltages vs. Junction Temperature

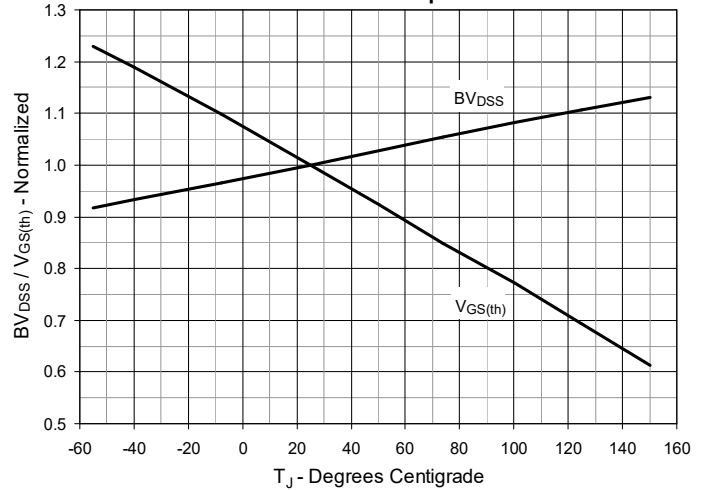


Fig. 7. Input Admittance

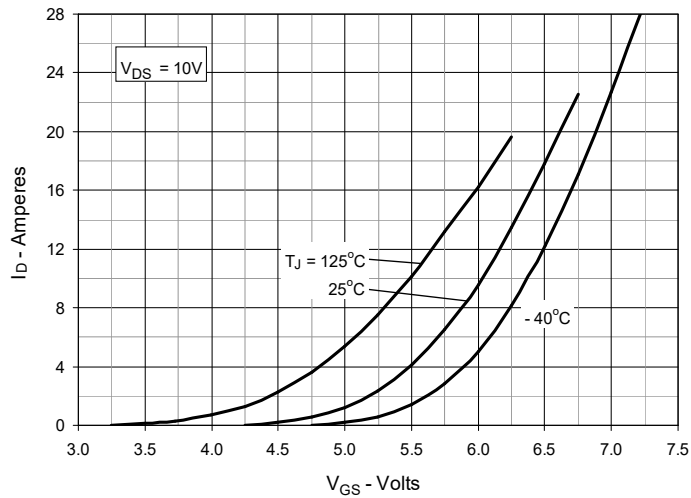


Fig. 8. Transconductance

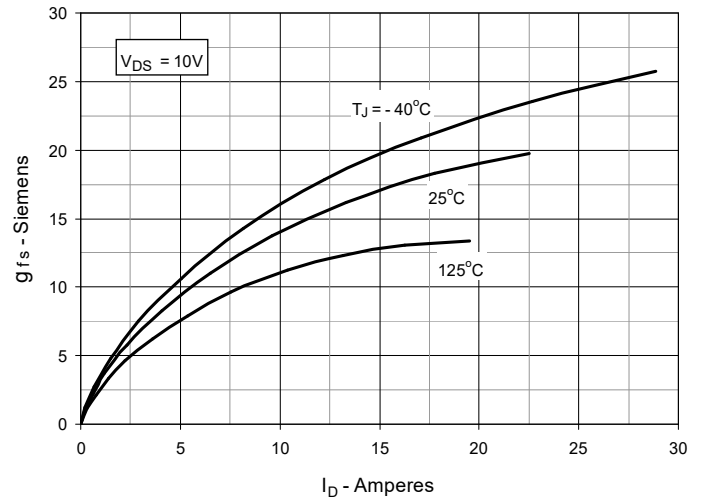


Fig. 9. Forward Voltage Drop of Intrinsic Diode

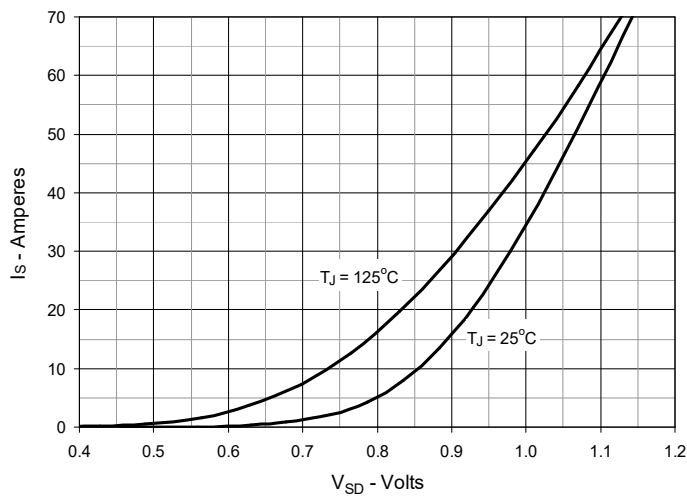


Fig. 10. Gate Charge

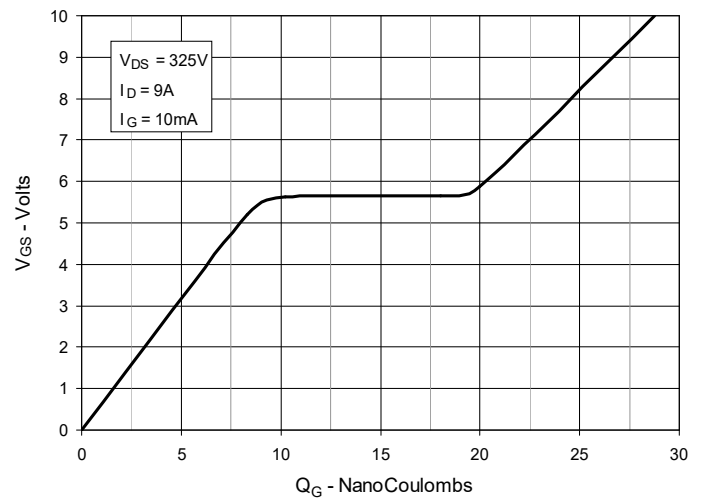


Fig. 11. Capacitance

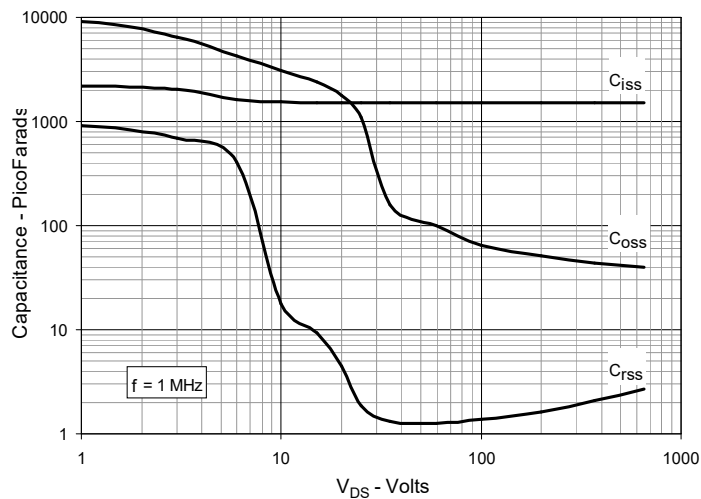


Fig. 12. Output Capacitance Stored Energy

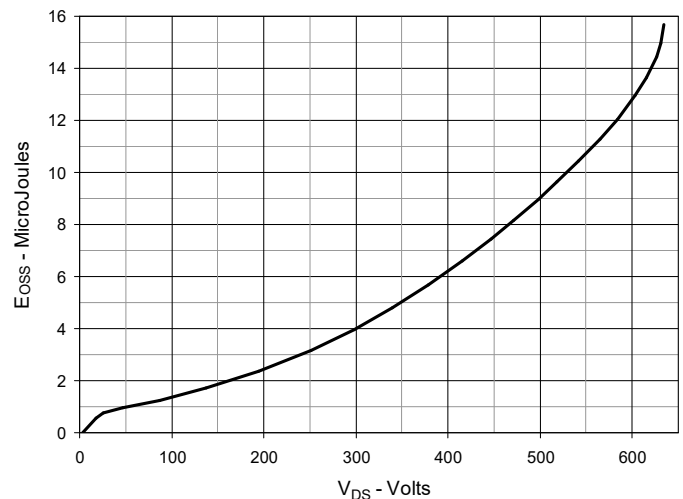
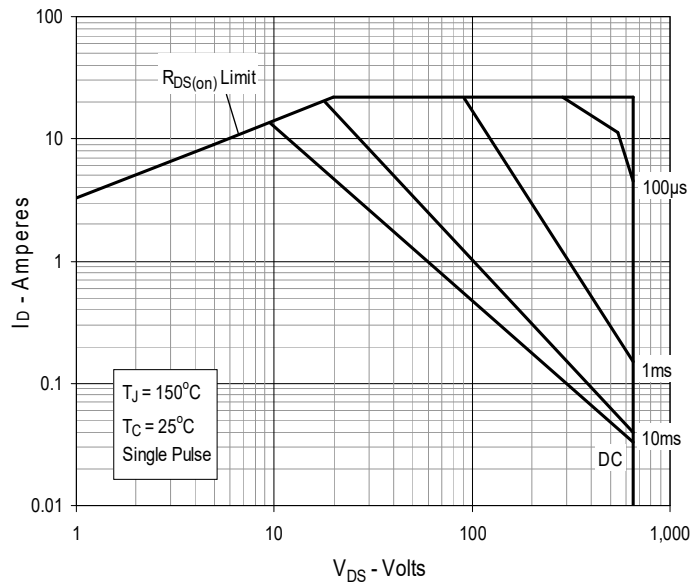


Fig. 13. Forward-Bias Safe Operating Area

Fig. 14. Maximum Transient Thermal Impedance
